

## isc N-Channel MOSFET Transistor

## IRL1404, IIRL1404

### • FEATURES

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 4.0m\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

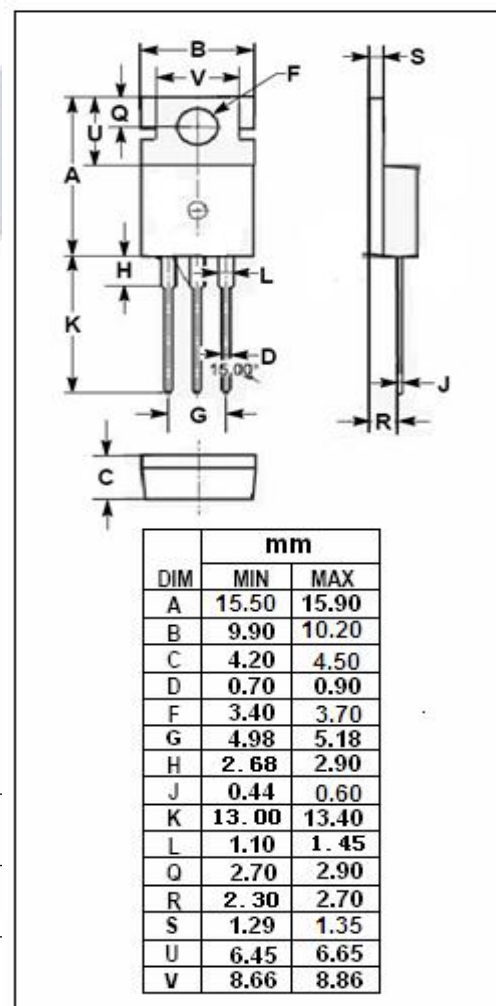
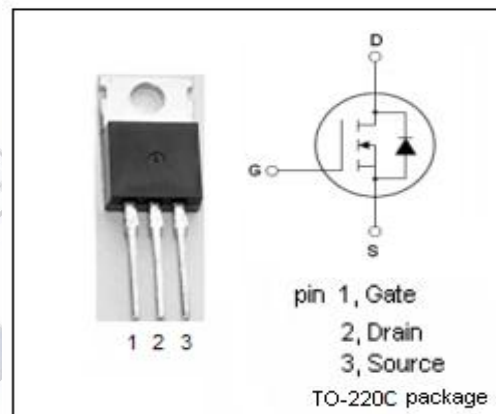
- Combine with the fast switching speed and ruggedized device design, provide the designer with an extremely efficient and reliable device for use in a wide variety of applications.

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	160	A
$I_{DM}$	Drain Current-Single Pulsed	640	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	200	W
$T_j$	Max. Operating Junction Temperature	175	$^\circ C$
$T_{stg}$	Storage Temperature	-55~175	$^\circ C$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.75	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^\circ C/W$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ ; $I_D=250\mu A$	40			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ ; $I_D=250\mu A$	1		3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V$ ; $I_D=95A$			4	$m\Omega$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$			$\pm 200$	nA
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=40V$ ; $V_{GS}=0V$			20	$\mu A$
$V_{SD}$	Diode forward voltage	$I_S=95A$ ; $V_{GS}=0V$			1.3	V